

	No.3453	2SK1450
	N-Channel MOS Silicon FET Very High-Speed Switching Applications	

Features

- Low ON-state resistance.
- Very high-speed switching, converters.

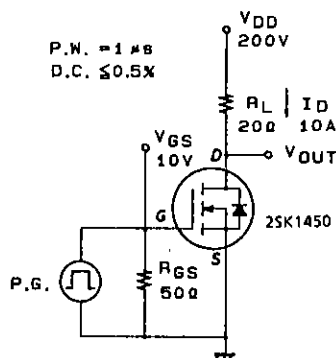
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Drain to Source Voltage	V_{DS}	450	V
Gate to Source Voltage	V_{GS}	± 30	V
Drain Current(DC)	I_D	20	A
Drain Current(Pulse)	I_{DP}	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	A
Allowable Power Dissipation	P_D	$T_c = 25^\circ\text{C}$	150 W
			2.5 W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	$-55 \text{ to } +150$	$^\circ\text{C}$

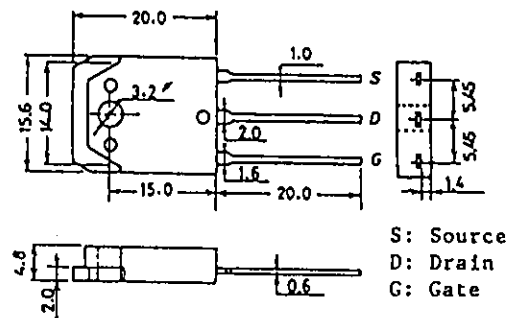
Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}, V_{GS} = 0$	450			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 450\text{V}, V_{GS} = 0$			1.0	mA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{V}, V_{DS} = 0$			± 100	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$	2.0		3.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, I_D = 10\text{A}$	7.5	15		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = 10\text{A}, V_{GS} = 10\text{V}$		0.24	0.3	Ω
Input Capacitance	C_{iss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$		3200		pF
Output Capacitance	C_{oss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$		440		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$		160		pF
Turn-ON Delay Time	$t_{d(on)}$	$I_D = 10\text{A}, V_{GS} = 10\text{V}$ $V_{DD} = 200\text{V}, R_{GS} = 50\Omega$		40		ns
Rise Time	t_r			100		ns
Turn-OFF Delay Time	$t_{d(off)}$			450		ns
Fall Time	t_f			150		ns
Diode Forward Voltage	V_{SD}	$I_S = 20\text{A}, V_{GS} = 0$			1.8	V

(Note) Be careful in handling the 2SK1450 because it has no protection diode between gate and source.

Switching Time Test Circuit**Package Dimensions 2056**

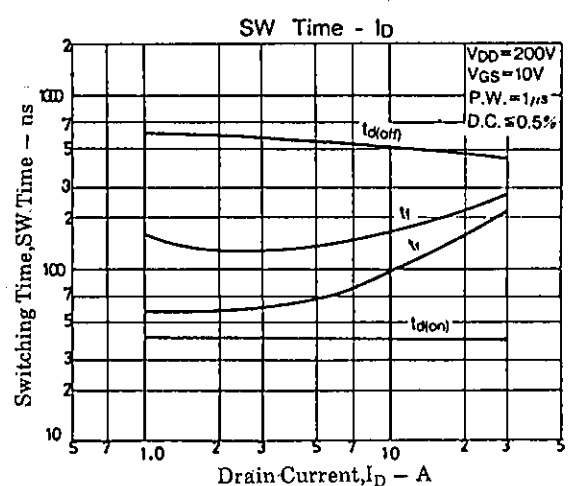
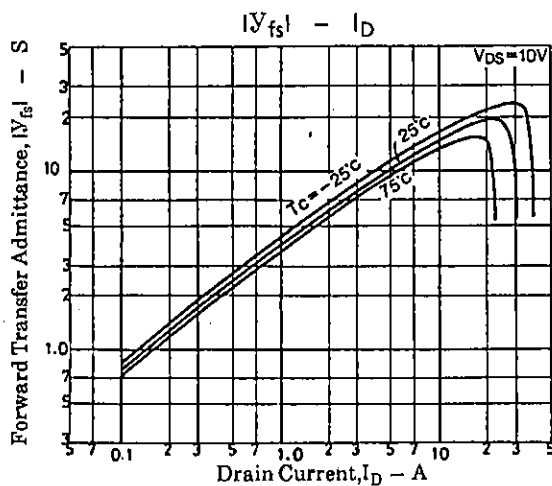
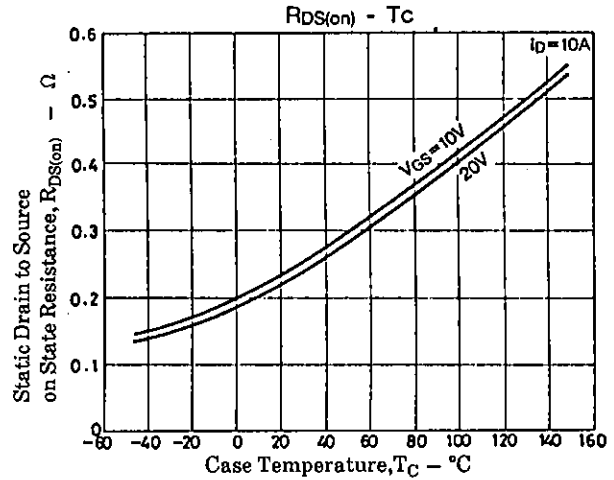
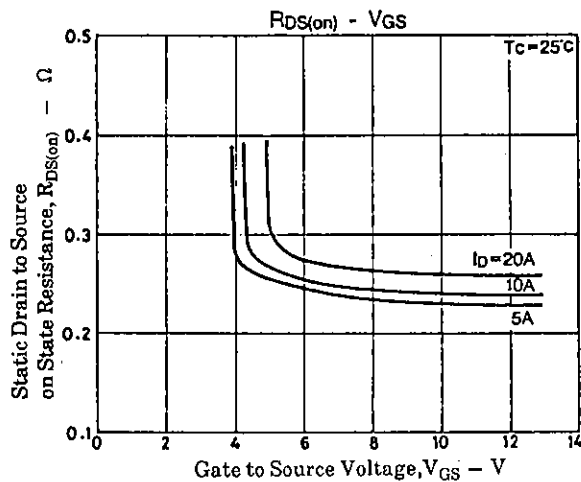
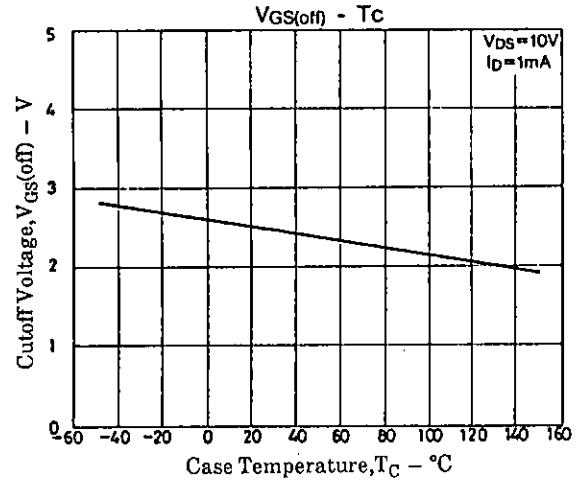
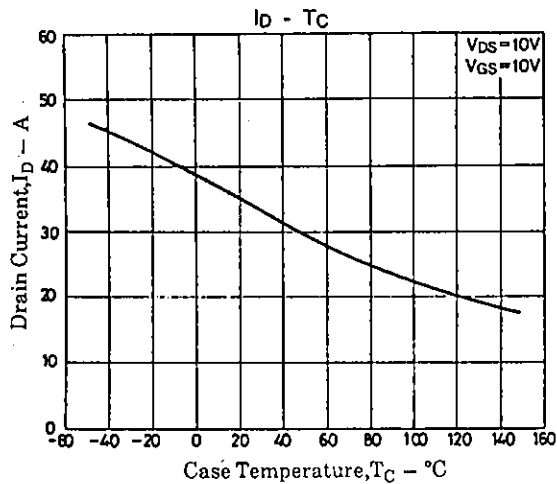
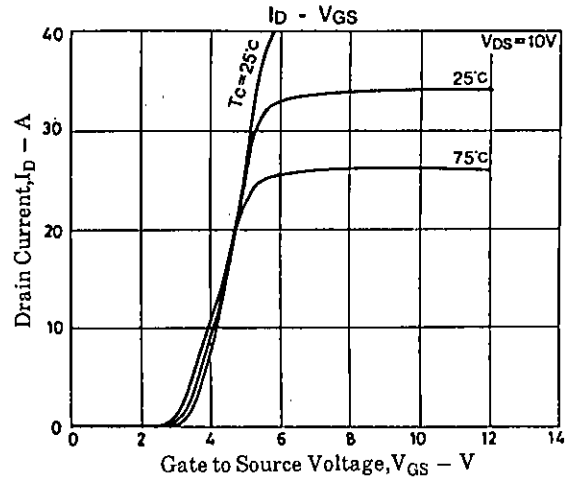
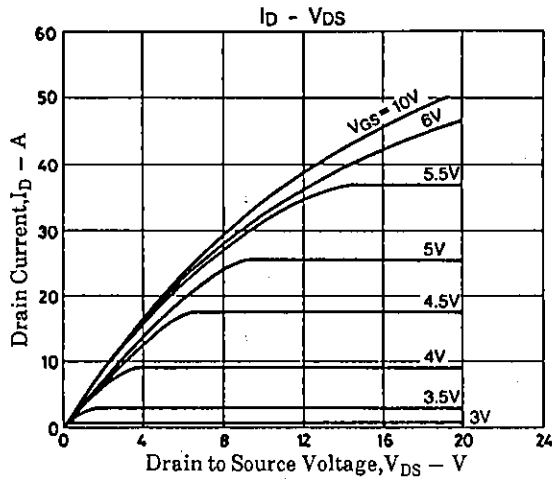
(unit: mm)

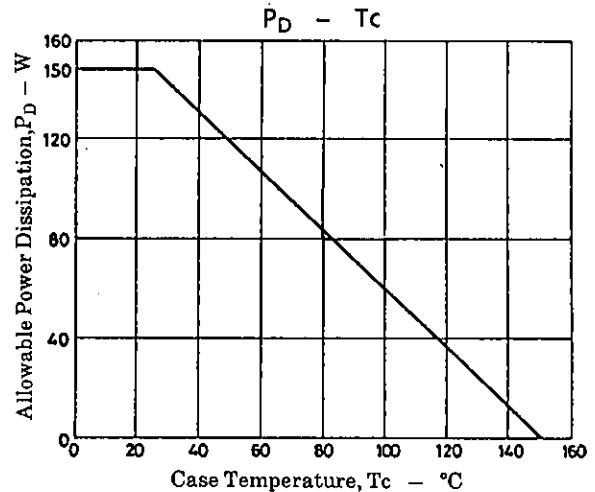
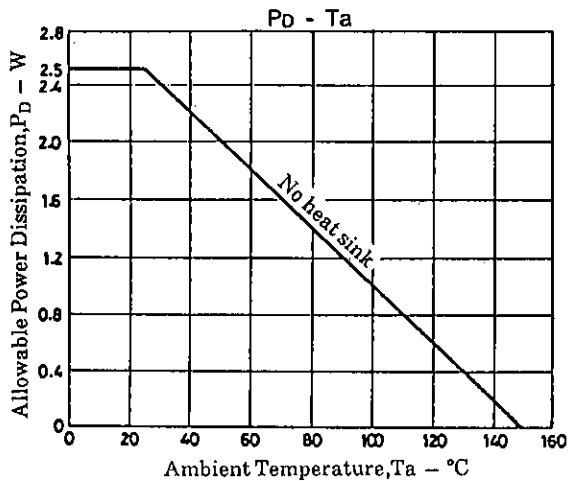
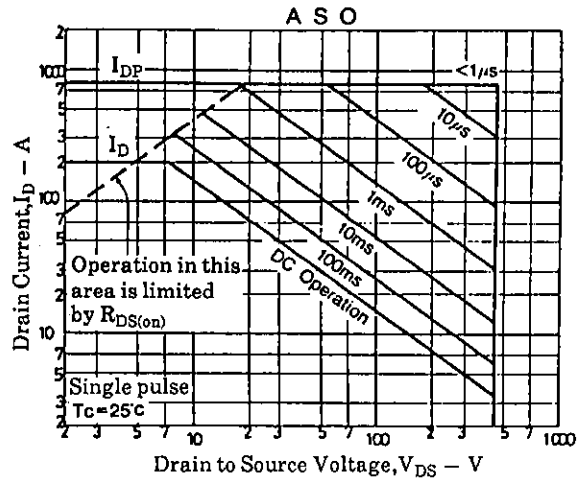
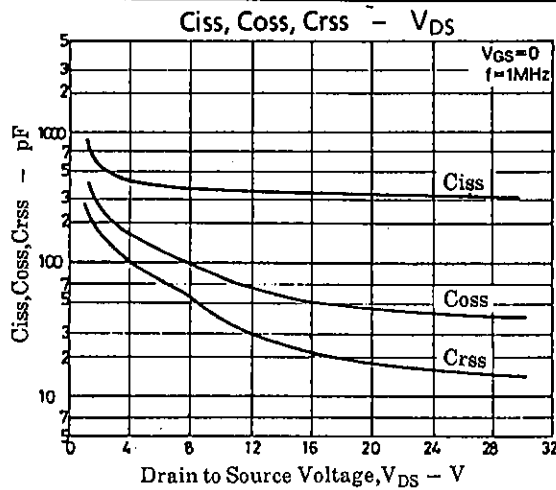


SANYO: TO3PB

SANYO Electric Co., Ltd. Semiconductor Business Headquarters
 TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

6131JN (KOTO) X-6827, 8035 No.3453-1/3





■ No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.

■ Anyone purchasing any products described or contained herein for an above-mentioned use shall:

- ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use;
- ② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.

■ Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.